

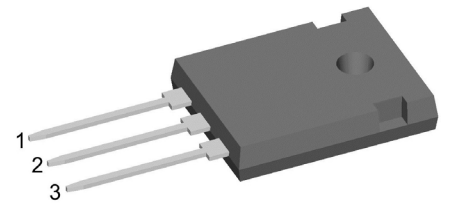
# SiC Schottky Diode

$$V_{RRM} = 2 \times 1200 \text{ V}$$

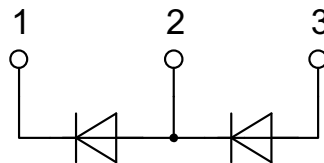
$$I_{FAV} = 18.5 \text{ A}$$

Ultra fast switching  
 Zero reverse recovery  
 Phase leg

Part number  
**DCG17P1200HR**



Backside: isolated  

### Features / Advantages:

- Ultra fast switching
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- Positive temperature coefficient of forward voltage
- $T_{VJM} = 175^{\circ}\text{C}$

### Applications:

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

### Package: ISO247

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

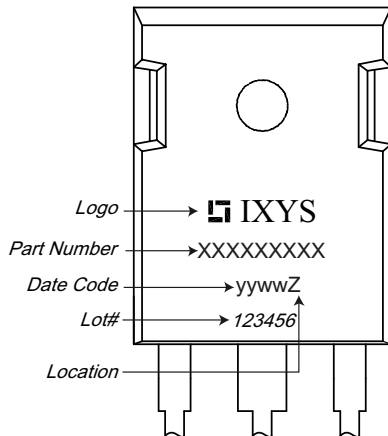
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SiC Diode (per diode)				Ratings				
Symbol	Definitions	Conditions	min.	typ.	max.			
$V_{RSM}$	max. non-repetitive reverse blocking voltage				1200	V		
$V_{RRM}$	max. repetitive reverse blocking voltage				1200	V		
$I_R$	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$		35	200	$\mu\text{A}$	
			$T_{VJ} = 175^\circ\text{C}$		65	400	$\mu\text{A}$	
$V_F$	forward voltage	$I_F = 20\text{ A}$ $I_F = 40\text{ A}$	$T_{VJ} = 25^\circ\text{C}$		1.5	1.8	V	
			$T_{VJ} = 175^\circ\text{C}$		2.2	3.0	V	
		$I_F = 20\text{ A}$ $I_F = 40\text{ A}$	rectangular, d = 0.5	$T_{VJ} = 25^\circ\text{C}$				
				$T_{VJ} = 175^\circ\text{C}$				
$I_{FAV}$	average forward current	$T_C = 80^\circ\text{C}$ $T_C = 100^\circ\text{C}$	}	$T_{VJ} = 175^\circ\text{C}$	18.5	A		
					17.0	A		
$I_{F25}$	forward current	based on typ. $V_{F0}$ and $r_F$	$T_C = 25^\circ\text{C}$		34	A		
$I_{F80}$			$T_C = 80^\circ\text{C}$		26.5	A		
$I_{F100}$			$T_C = 100^\circ\text{C}$		23	A		
$I_{FSM}$	max forward surge current	t = 10 ms, half sine (50 Hz) $t_p = 10\ \mu\text{s}$ , pulse	}	$T_{VJ} = 25^\circ\text{C}$ $V_R = 0\text{V}$				
					1000	A		
$V_{F0}$	threshold voltage	} for power loss calculation		$T_{VJ} = 125^\circ\text{C}$ $175^\circ\text{C}$	0.78	V		
$r_F$	slope resistance				$T_{VJ} = 125^\circ\text{C}$	0.73	V	
					$T_{VJ} = 175^\circ\text{C}$	57.0	$\text{m}\Omega$	
						70.5	$\text{m}\Omega$	
$Q_C$	total capacitive charge	$V_R = 800\text{ V}$ , $I_F = 20\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		99	nC		
$C$	total capacitance	$V_R = 0\text{ V}$ $V_R = 400\text{ V}$ $V_R = 800\text{ V}$	}	$T_{VJ} = 25^\circ\text{C}$ , f = 1 MHz	1500	pF		
					93	pF		
					67	pF		
$R_{thJC}$	thermal resistance junction to case	with heatsink compound; IXYS test setup			1.4	K/W		
$R_{thJH}$	thermal resistance junction to heatsink				1.6	K/W		

Package ISO247			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
$I_{RMS}$	RMS current	per terminal			70	A
$T_{stg}$	storage temperature		-40		150	°C
$T_{op}$	operation temperature		-40		150	°C
$T_{VJ}$	virtual junction temperature		-40		175	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		40		120	N
$d_{Spp/App}$	creepage distance on surface /	terminal to terminal	2.7			mm
$d_{Spb/Appb}$	striking distance through air	terminal to backside	4.1			mm
$V_{ISOL}$	isolation voltage	$t = 1$ second $t = 1$ minute		3600 3000		V V
			50/60 Hz; RMS; $I_{ISOL} < 1$ mA			

### Product Marking

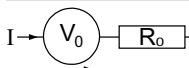


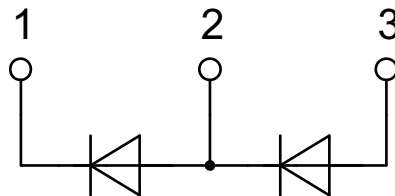
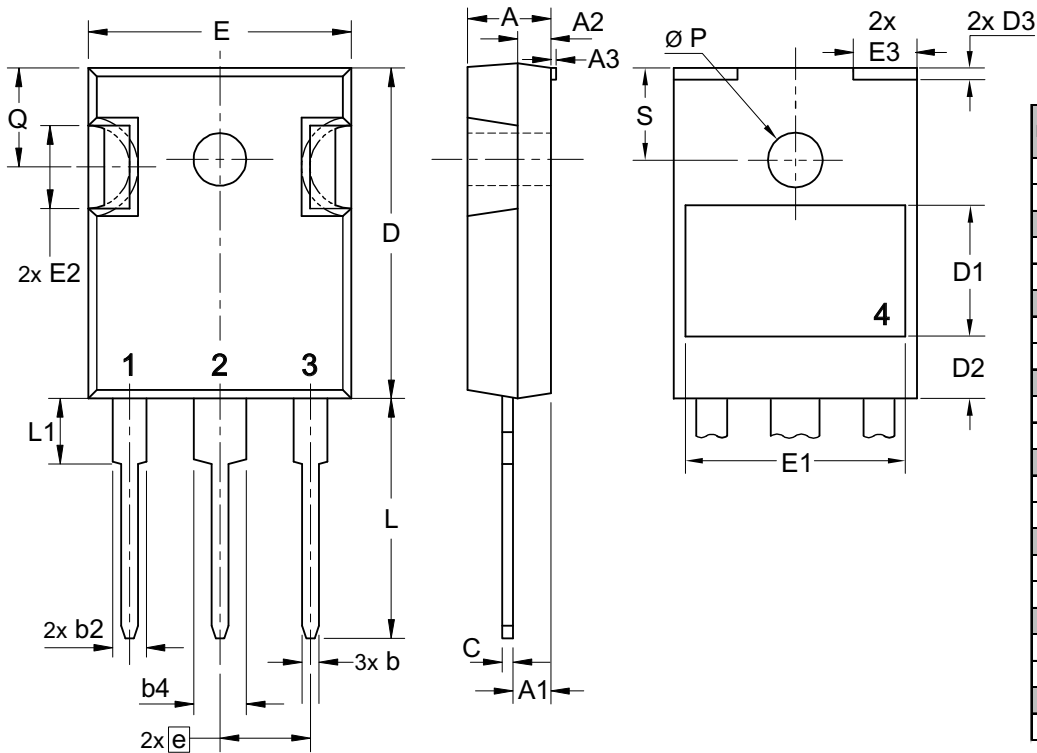
### Part description

D = Diode  
 C = SiC  
 G = Extreme fast  
 17 = Current Rating [A]  
 P = Phase leg  
 1200 = Reverse Voltage [V]  
 HR = ISO247 (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG17P1200HR	DCG17P1200HR	Tube	30	DCG17P1200HR

### Equivalent Circuits for Simulation \*on die level, typical

		$T_{VJ} = 125^{\circ}\text{C}$	$T_{VJ} = 175^{\circ}\text{C}$	
$V_{0\max}$	threshold voltage	0.78	0.73	V
$R_{0\max}$	slope resistance *	57.0	70.5	mΩ

**Outlines ISO247**


**SiC Diode (per diode)**

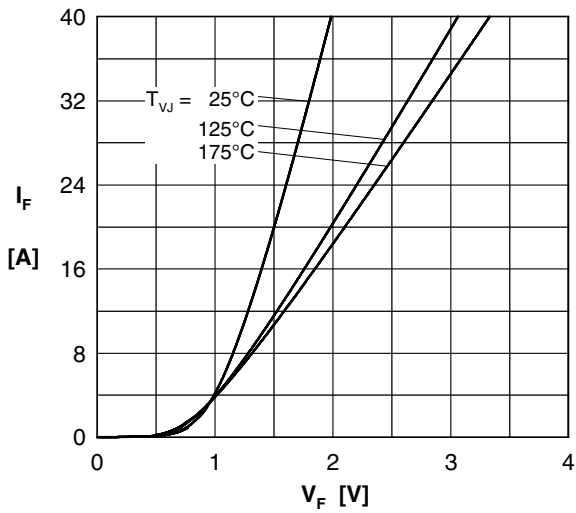


Fig. 1 Typ. forward characteristics.

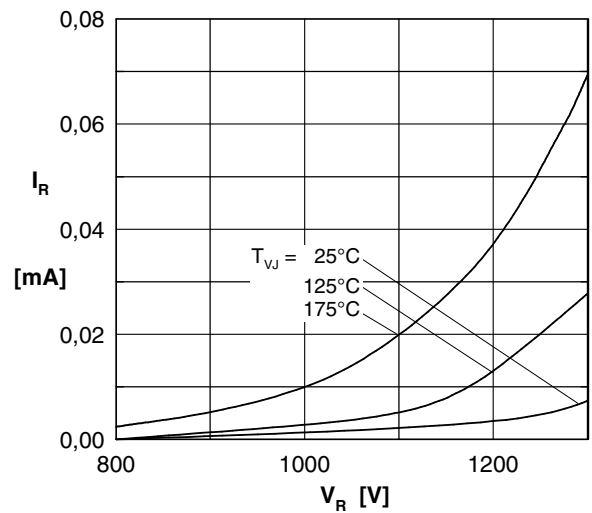


Fig. 2 Typ. reverse characteristics

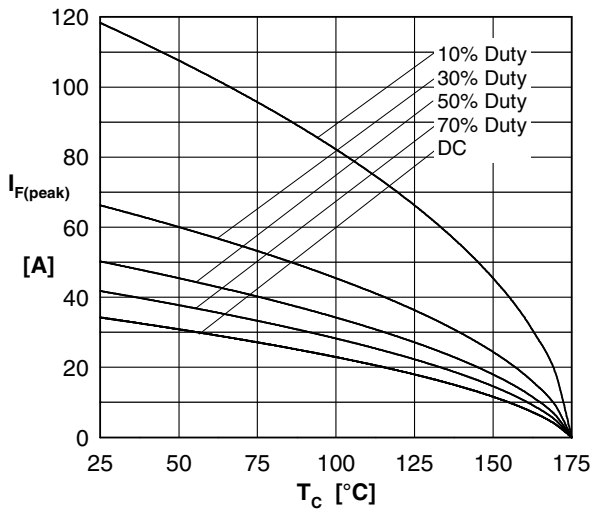


Fig. 3 Typ. current derating

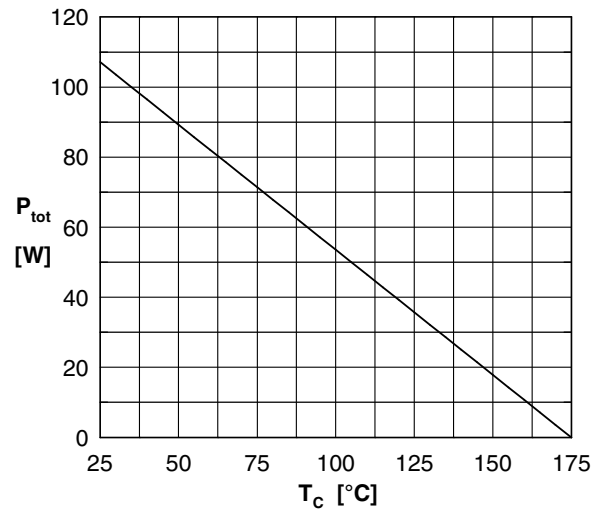


Fig. 4 Power derating

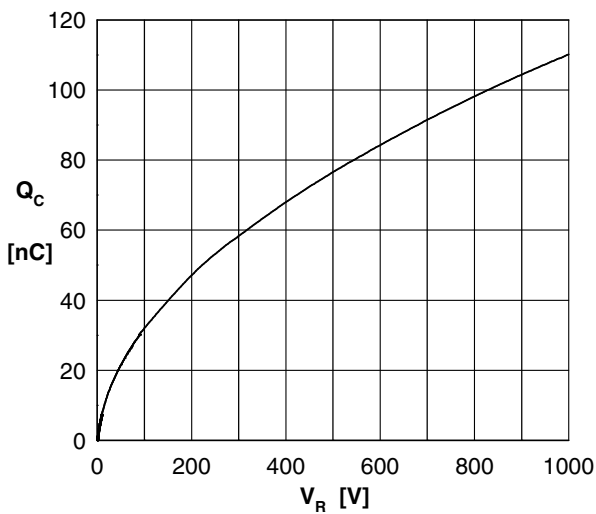


Fig. 5 Typ. recovery charge vs. reverse voltage

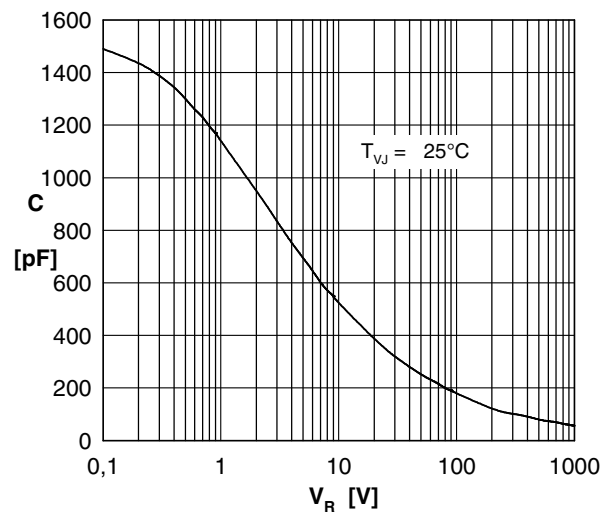


Fig. 6 Typ. junction capacitance vs. reverse Voltage

**SiC Diode (per diode)**

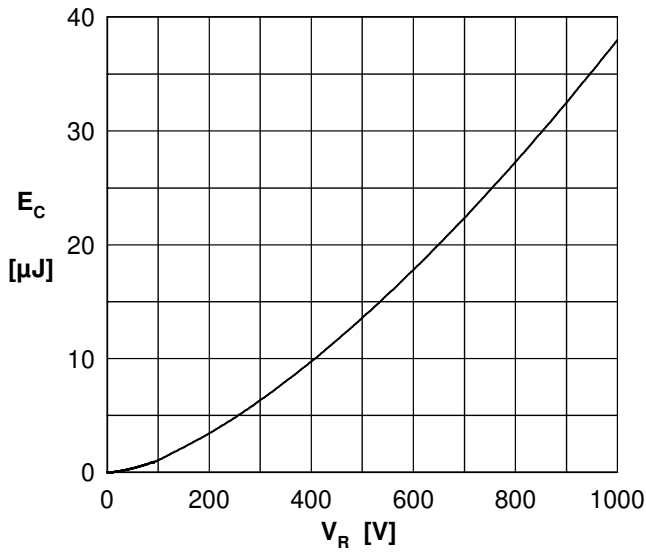


Fig. 7 Typical capacitance stored energy

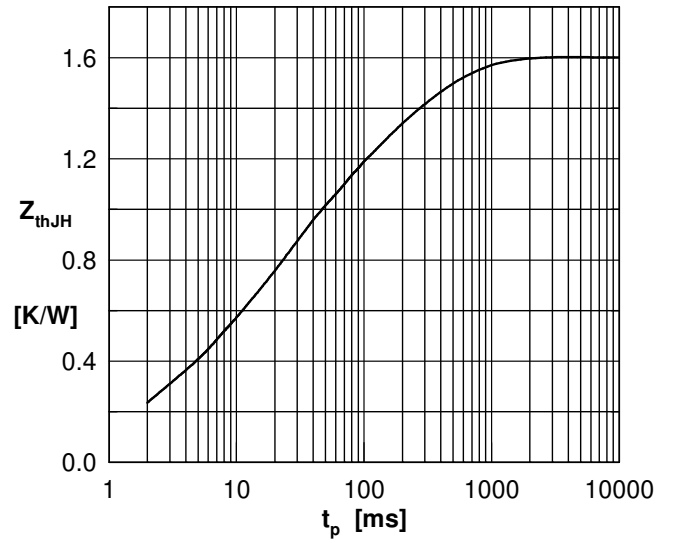


Fig. 8 Typ. transient thermal impedance junction to heatsink